

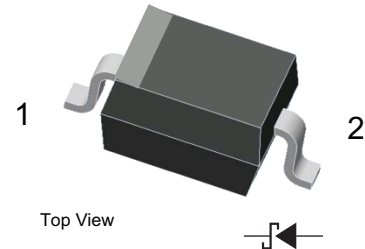
Schottky Diodes

BAT760

■ Features

- Very Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance

SOD-323



PIN DESCRIPTION

PIN	DESCRIPTION
1	Cathode
2	Anode

■ Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	21	
Average Rectified Output Current	I_O	1	A
Forward Current $t = 8.3$ ms Half Sinewave	I_{FSM}	5.5	
Power Dissipation	P_D	235	mW
Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	426	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

Note 1: Part mounted on FR-4 PC board with recommended pad layout

■ Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

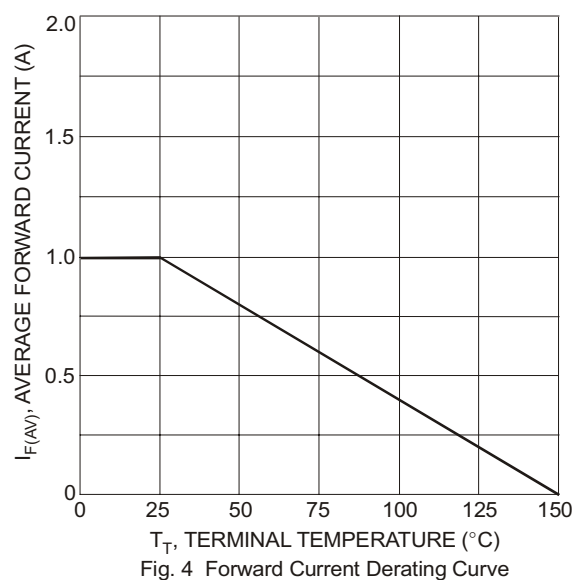
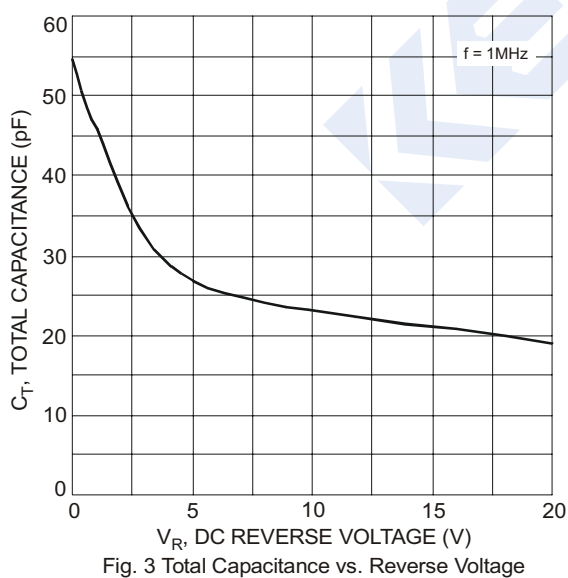
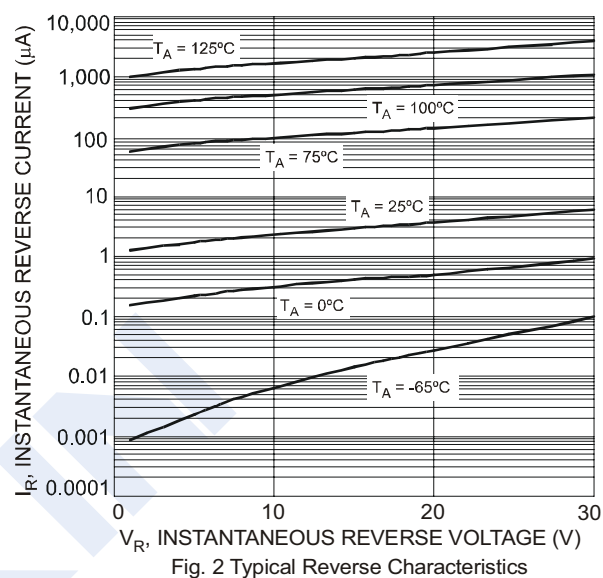
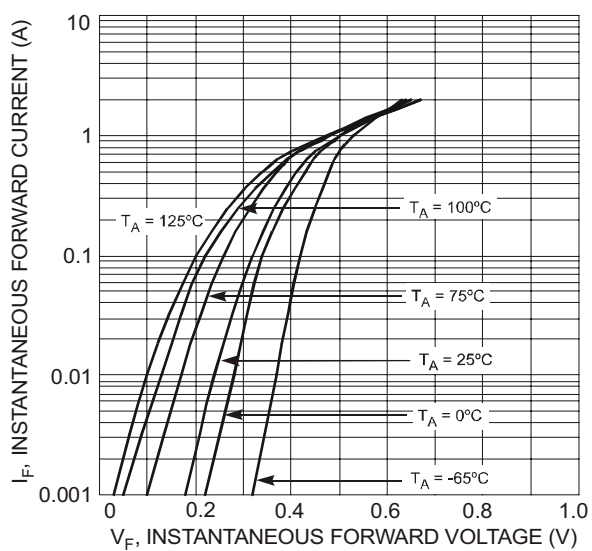
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage (Note 2)	V_R	$I_R = 500 \mu\text{A}$	30			V
Forward voltage	V_{F1}	$I_F = 10 \text{ mA}$			0.27	
	V_{F2}	$I_F = 100 \text{ mA}$			0.35	
	V_{F3}	$I_F = 1 \text{ A}$			0.55	
Leakage current (Note 2)	I_{R1}	$V_R = 5 \text{ V}$			10	μA
	I_{R2}	$V_R = 8 \text{ V}$			20	
	I_{R3}	$V_R = 15 \text{ V}$			50	
Total Capacitance	C_T	$V_R = 5 \text{ V}, f = 1 \text{ MHz}$		25		pF

Note 2: Short duration pulse test used to minimize self-heating effect.

Schottky Diodes

BAT760

■ Typical Characteristics



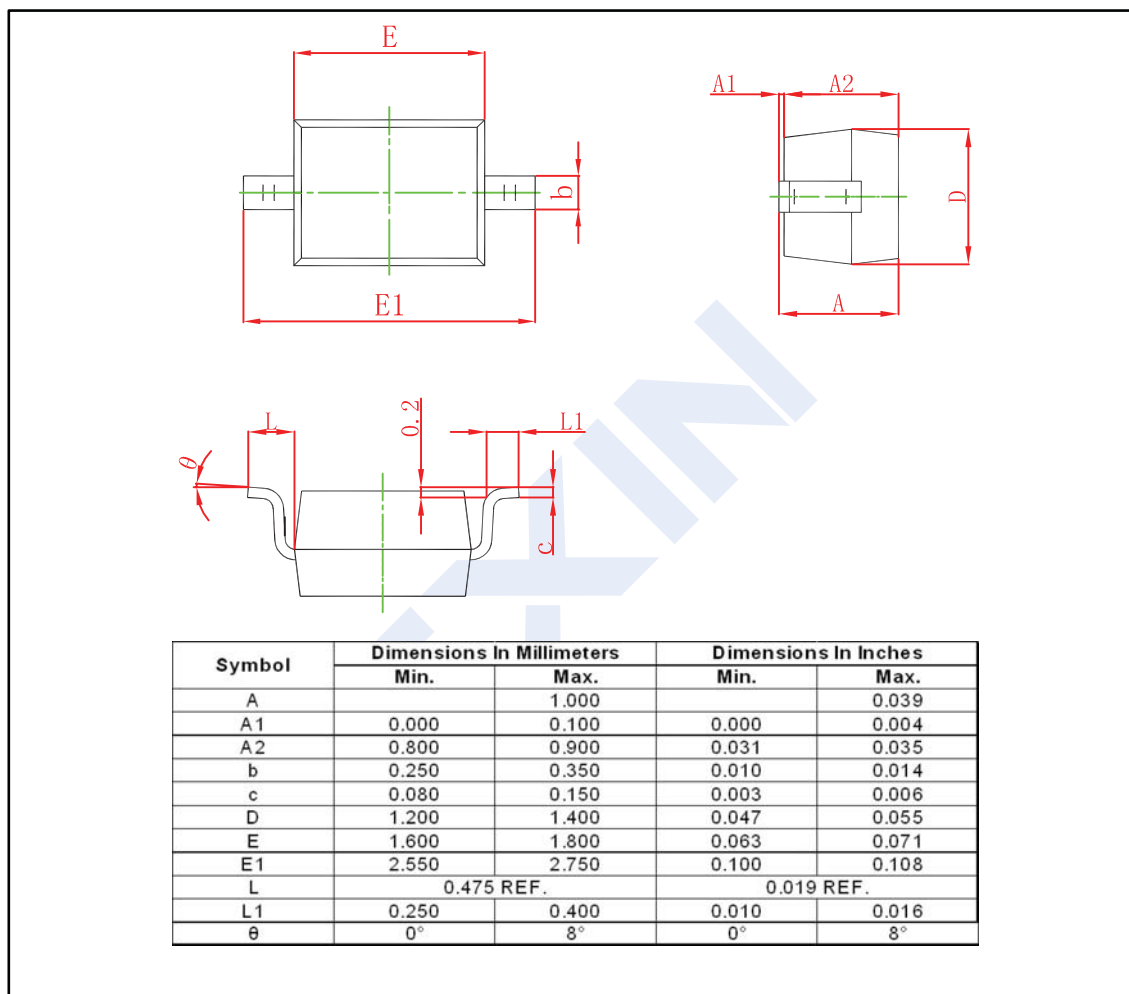
Schottky Diodes

BAT760

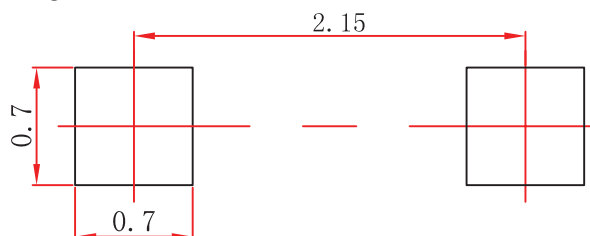
■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-323



■ The Recommended Mounting Pad Size

**Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.